

TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

TC74HC148AP, TC74HC148AF**8 - TO - 3 LINE PRIORITY ENCODER**

The TC74HC148A is a high speed CMOS 8 - to - 3 LINE ENCODER fabricated with silicon gate C2MOS technology.

It achieves the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

All data inputs and outputs of these encoders are active at the low logic level.

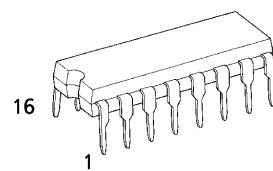
The encoder detects a low level of the highest order among eight input singals and outputs the corresponding signal position in binaly code.

Enable Input EI and Enable Output EO are used to easily cascade without using external circuits.

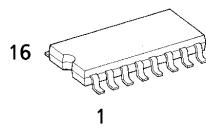
All inputs are equipped with protection circuits against static discharge or transient excess voltage.

FEATURES :

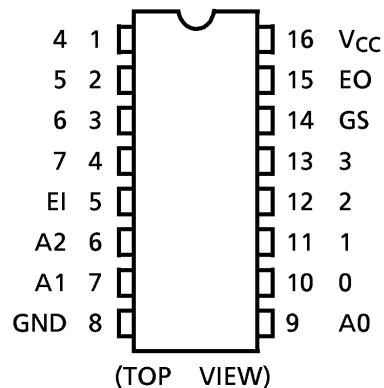
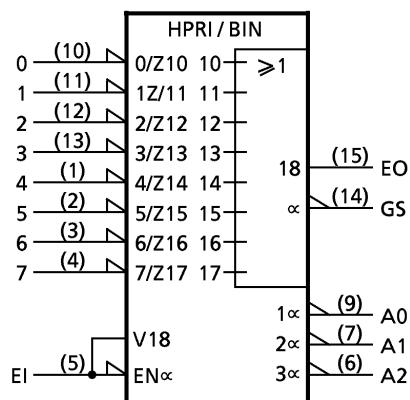
- High Speed..... $t_{pd} = 15\text{ns}(\text{typ.})$ at $V_{CC} = 5\text{V}$
- Low Power Dissipation..... $I_{CC} = 4\mu\text{A}(\text{Max.})$ at $T_a = 25^\circ\text{C}$
- High Noise Immunity..... $V_{NIH} = V_{NIL} = 28\% V_{CC}$ (Min.)
- Output Drive Capability.....10 LSTTL Loads
- Symmetrical Output Impedance..... $|I_{OH}| = I_{OL} = 4\text{mA}(\text{Min.})$
- Balanced Propagation Delays..... $t_{pLH} \approx t_{pHL}$
- Wide Operating Voltage Range..... $V_{CC} (\text{opr.}) = 2\text{V} \sim 6\text{V}$
- Pin and Function Compatible with 74LS148



P (DIP16-P-300-2.54A)
Weight : 1.00g (Typ.)



F (SOP16-P-300-1.27)
Weight : 0.18g (Typ.)

PIN ASSIGNMENT**IEC LOGIC SYMBOL**

961001EBA2

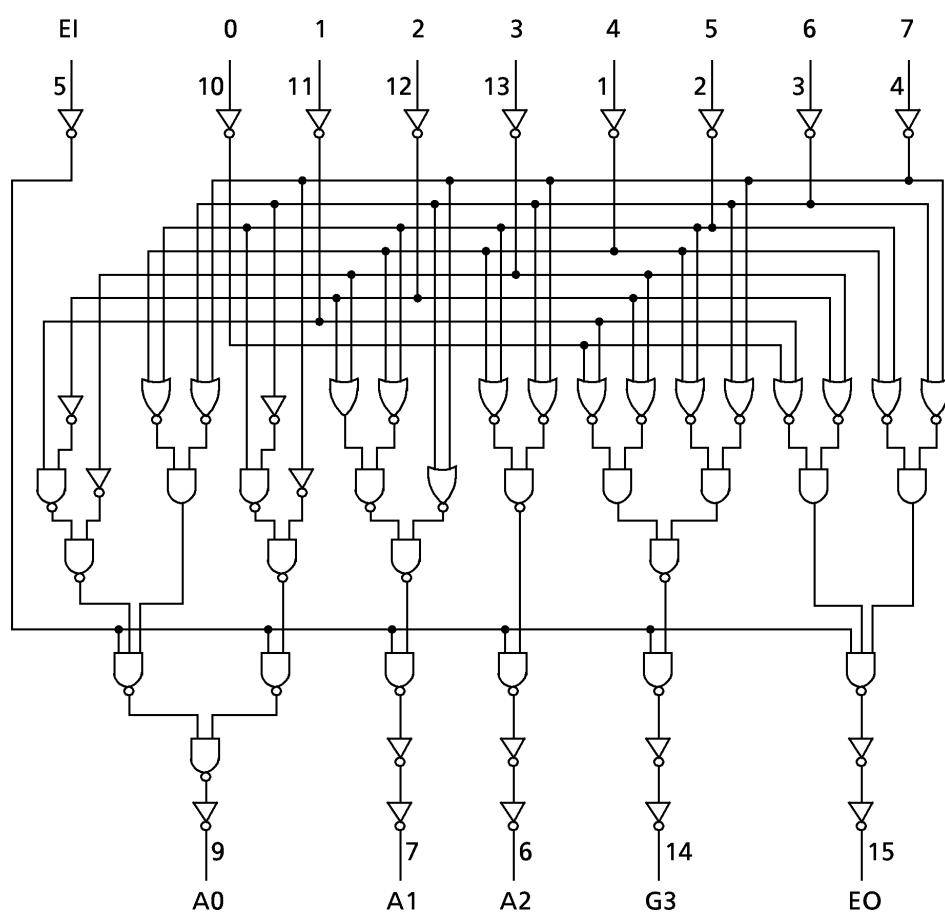
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TRUTH TABLE

EI	INPUTS								OUTPUTS				
	0	1	2	3	4	5	6	7	A2	A1	A0	GS	EO
H	X	X	X	X	X	X	X	X	H	H	H	H	H
L	H	H	H	H	H	H	H	H	H	H	H	H	L
L	X	X	X	X	X	X	X	L	L	L	L	L	H
L	X	X	X	X	X	X	L	H	L	L	H	L	H
L	X	X	X	X	X	L	H	H	L	H	L	L	H
L	X	X	X	X	L	H	H	H	H	L	H	L	H
L	X	X	X	L	H	H	H	H	H	L	H	L	H
L	X	L	H	H	H	H	H	H	H	H	L	L	H
L	L	H	H	H	H	H	H	H	H	H	H	L	H

X : Don't care

SYSTEM DIAGRAM



961001EBA2'

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V_{CC}	-0.5~7	V
DC Input Voltage	V_{IN}	-0.5~ $V_{CC} + 0.5$	V
DC Output Voltage	V_{OUT}	-0.5~ $V_{CC} + 0.5$	V
Input Diode Current	I_{IK}	± 20	mA
Output Diode Current	I_{OK}	± 20	mA
DC Output Current	I_{OUT}	± 25	mA
DC V_{CC} / Ground Current	I_{CC}	± 50	mA
Power Dissipation	P_D	500 (DIP)* / 180 (SOP)	mW
Storage Temperature	T_{stg}	-65~150	°C

*500mW in the range of $T_a = -40^{\circ}\text{C} \sim 65^{\circ}\text{C}$. From $T_a = 65^{\circ}\text{C}$ to 85°C a derating factor of $-10\text{mW}/^{\circ}\text{C}$ shall be applied until 300mW.

RECOMMENDED OPERATING CONDITIONS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V_{CC}	2~6	V
Input Voltage	V_{IN}	0~ V_{CC}	V
Output Voltage	V_{OUT}	0~ V_{CC}	V
Operating Temperature	T_{opr}	-40~85	°C
Input Rise and Fall Time	t_r, t_f	0~1000 ($V_{CC} = 2.0\text{V}$) 0~500 ($V_{CC} = 4.5\text{V}$) 0~400 ($V_{CC} = 6.0\text{V}$)	ns

DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL	TEST CONDITION	V_{CC} (V)	Ta = 25°C			Ta = -40~85°C		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
High - Level Input Voltage	V_{IH}		2.0 4.5 6.0	1.50 3.15 4.20	— — —	— — —	1.50 3.15 4.20	— — —	V
Low - Level Input Voltage	V_{IL}		2.0 4.5 6.0	— — —	— — —	0.50 1.35 1.80	— — —	0.50 1.35 1.80	V
High - Level Output Voltage	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -20\mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	— — —	1.9 4.4 5.9	— — —
			$I_{OH} = -4\text{ mA}$ $I_{OH} = -5.2\text{ mA}$	4.5 6.0	4.18 5.68	4.31 5.80	— —	4.13 5.63	— —
Low - Level Output Voltage	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 20\mu\text{A}$	2.0 4.5 6.0	0.0 0.0 0.0	0.1 0.1 0.1	— — —	0.1 0.1 0.1	— — —
			$I_{OL} = 4\text{ mA}$ $I_{OL} = 5.2\text{ mA}$	4.5 6.0	0.17 0.18	0.26 0.26	— —	0.33 0.33	— —
Input Leakage Current	I_{IN}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	± 0.1	—	± 1.0	μA
Quiescent Supply Current	I_{CC}	$V_{IN} = V_{CC}$ or GND	6.0	—	—	4.0	—	40.0	

AC ELECTRICAL CHARACTERISTICS ($C_L = 15\text{pF}$, $V_{CC} = 5\text{V}$, $T_a = 25^\circ\text{C}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Output Transition Time	t_{TLH} t_{THL}		—	4	8	ns
Propagation Delay Time (IN—A0, A1, A2)	t_{PLH} t_{PHL}		—	15	25	
Propagation Delay Time (IN—EO, GS)	t_{PLH} t_{PHL}		—	15	25	
Propagation Delay Time (EI—EO)	t_{PLH} t_{PHL}		—	11	19	
Propagation Delay Time (EI—GS)	t_{PLH} t_{PHL}		—	11	19	
Propagation Delay Time (EI—A0, A1, A2)	t_{PLH} t_{PHL}		—	11	19	

AC ELECTRICAL CHARACTERISTICS ($C_L = 50\text{pF}$, Input $t_r = t_f = 6\text{ns}$)

PARAMETER	SYMBOL	TEST CONDITION	$V_{CC}(\text{V})$	$T_a = 25^\circ\text{C}$			$T_a = -40\text{--}85^\circ\text{C}$		UNIT
				MIN.	TYP.	MAX.	MIN.	MAX.	
Output Transition Time	t_{TLH} t_{THL}		2.0	—	30	75	—	95	ns
			4.5	—	8	15	—	19	
			6.0	—	7	13	—	16	
	t_{PLH} t_{PHL}		2.0	—	52	150	—	190	
			4.5	—	19	30	—	38	
			6.0	—	15	26	—	33	
Propagation Delay Time (IN—EO, GS)	t_{PLH} t_{PHL}		2.0	—	52	150	—	190	ns
			4.5	—	19	30	—	38	
			6.0	—	15	26	—	33	
	t_{PLH} t_{PHL}		2.0	—	40	115	—	145	
			4.5	—	14	23	—	29	
			6.0	—	11	20	—	25	
Propagation Delay Time (EI—GS)	t_{PLH} t_{PHL}		2.0	—	40	115	—	145	ns
			4.5	—	14	23	—	29	
			6.0	—	12	20	—	25	
	t_{PLH} t_{PHL}		2.0	—	40	115	—	145	
			4.5	—	14	23	—	29	
			6.0	—	12	20	—	25	
Input Capacitance	C_{IN}				—	5	10	—	10
Power Dissipation Capacitance	$C_{PD}(1)$				—	55	—	—	—

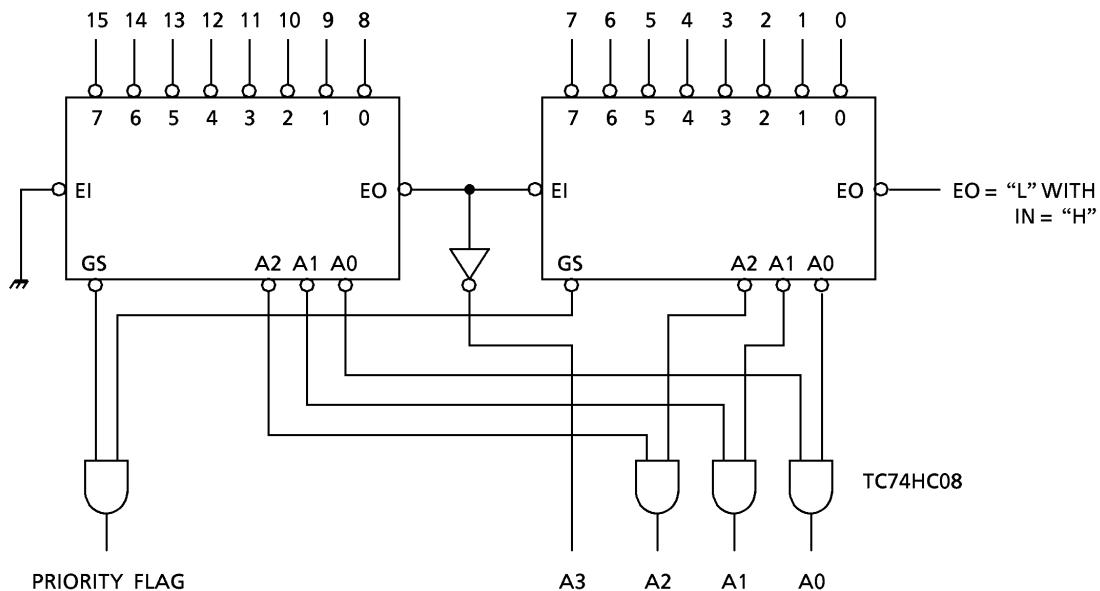
Note (1) C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :

$$I_{CC(\text{opr})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$$

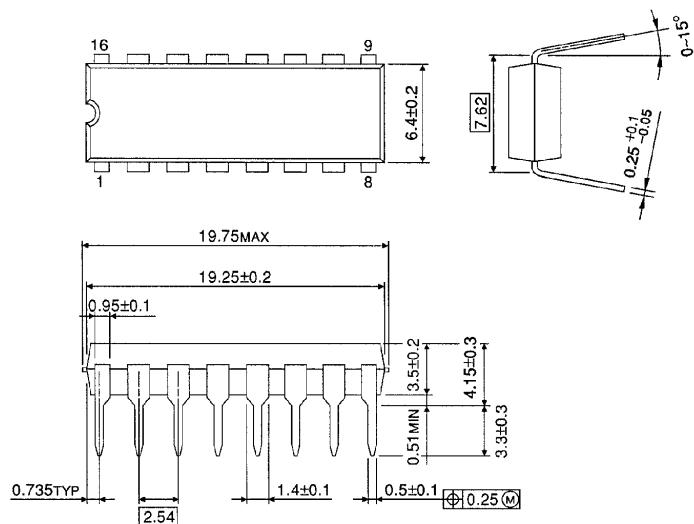
TYPICAL APPLICATION

4-BIT CASCADE CONNECTION



DIP 16PIN OUTLINE DRAWING (DIP16-P-300-2.54A)

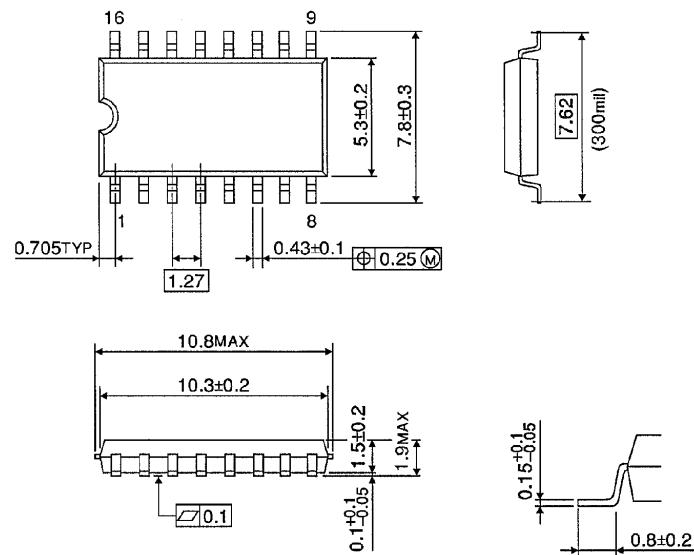
Unit in mm



Weight : 1.00g (Typ.)

SOP 16PIN (200mil BODY) OUTLINE DRAWING (SOP16-P-300-1.27)

Unit in mm



Weight : 0.18g (Typ.)